(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
27 May 2010 (27.05.2010)

PCT

(10) International Publication Number
WO 2010/059131 A1

(51) International Patent Classification:
H01L 21/311 (2006.01) *H01L 21/31* (2006.01)
H01L 21/20 (2006.01)

(21) International Application Number:
PCT/SG2009/000435

(22) International Filing Date:
19 November 2009 (19.11.2009)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
61/116,068 19 November 2008 (19.11.2008) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report (Art. 21(3))*

WO 2010/059131 A1

(54) Title: METHOD OF AT LEAST PARTIALLY RELEASING AN EPITAXIAL LAYER

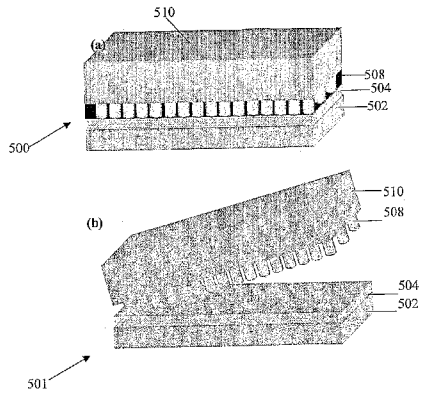


Figure 5

(57) Abstract: A method of at least partially releasing an epitaxial layer of a material from a substrate. The method comprises the steps of: forming a patterned sacrificial layer on the substrate such that the substrate is partially exposed and partially covered by the sacrificial layer; growing the epitaxial layer on the patterned sacrificial layer by nano-epitaxial lateral overgrowth such that the epitaxial layer is formed above an intermediate layer comprising the patterned sacrificial layer and said material; and selectively etching the patterned sacrificial layer such that the epitaxial layer is at least partially released from the substrate.